

Features

- Half-bridge SCR configuration integrated in a single package
- With high thermal conductivity DBC as the Insulation
- Welding by vacuum welding technology, which provide

Product Summary

Parameter	Conditions	Symbol	Values	Unit
Repetitive peak off-state voltage	Tvj = 25°C	V _{DRM}	1600	V
Repetitive peak reverse voltage	Tvj = 25°C	V _{RRM}	1600	V
Non-repetitive peak off-state voltage	Tvj = 25°C	V _{DSM}	1700	V
Non-repetitive peak reverse voltage	Tvj = 25°C	V _{RSM}	1700	V
Average forward current	T _C = 85°C	I _{T(AV)}	250	A
Forward surge current	t _P =10ms V _R =0.6VRRM	I _{TSM}	8300	A
I ² t value for fusing		I ² t	344450	A ² s

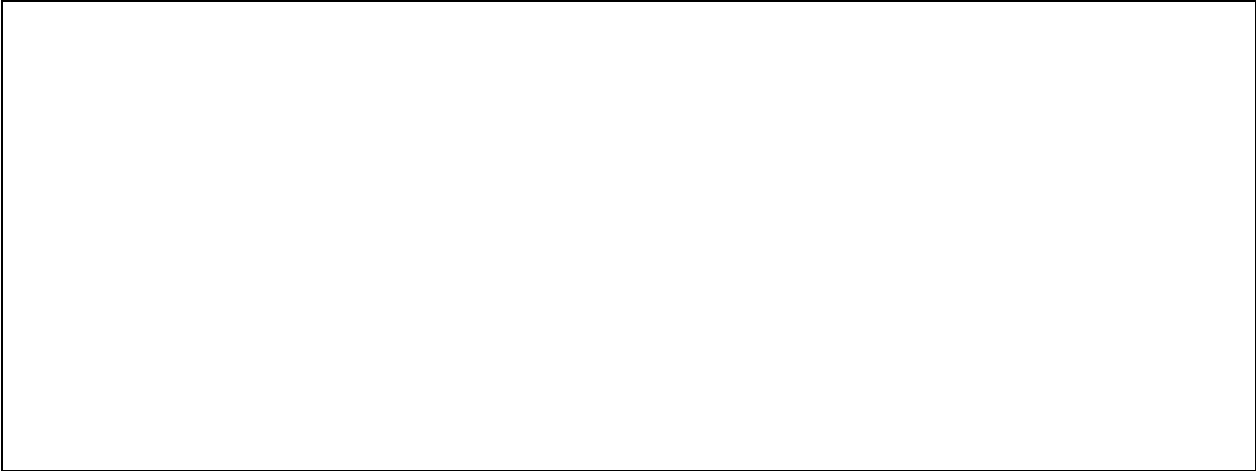
Critical rate of rise of on-state current I_G

Electrical Characteristics (@ T_C = 25°C unless otherwise specified)

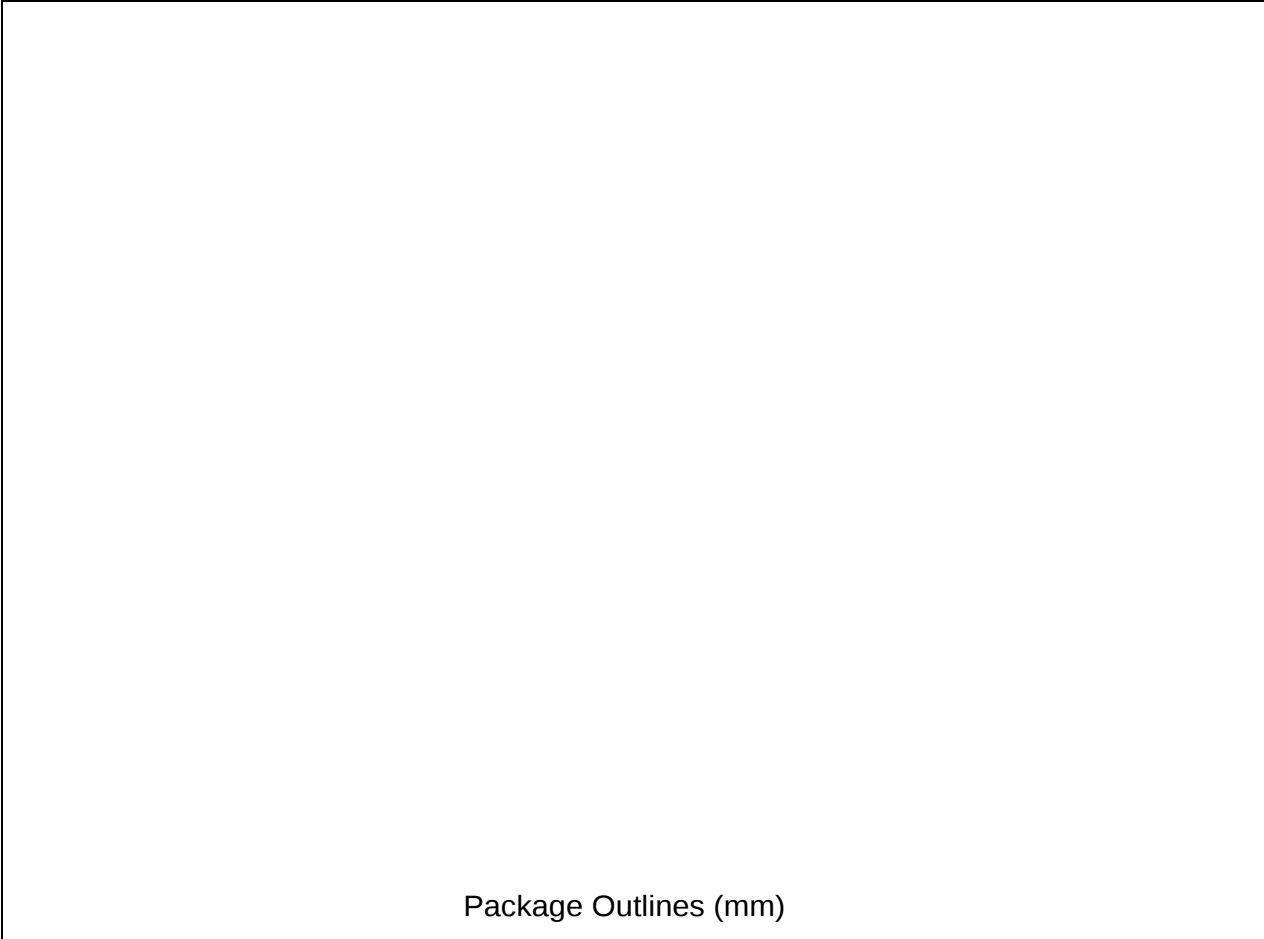
Parameter	Conditions	Symbol	Values			Unit
			Min.	Typ.	Max.	

Peak forward voltage	I _T =750					
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Circuit Diagram



Package Outlines (mm)



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